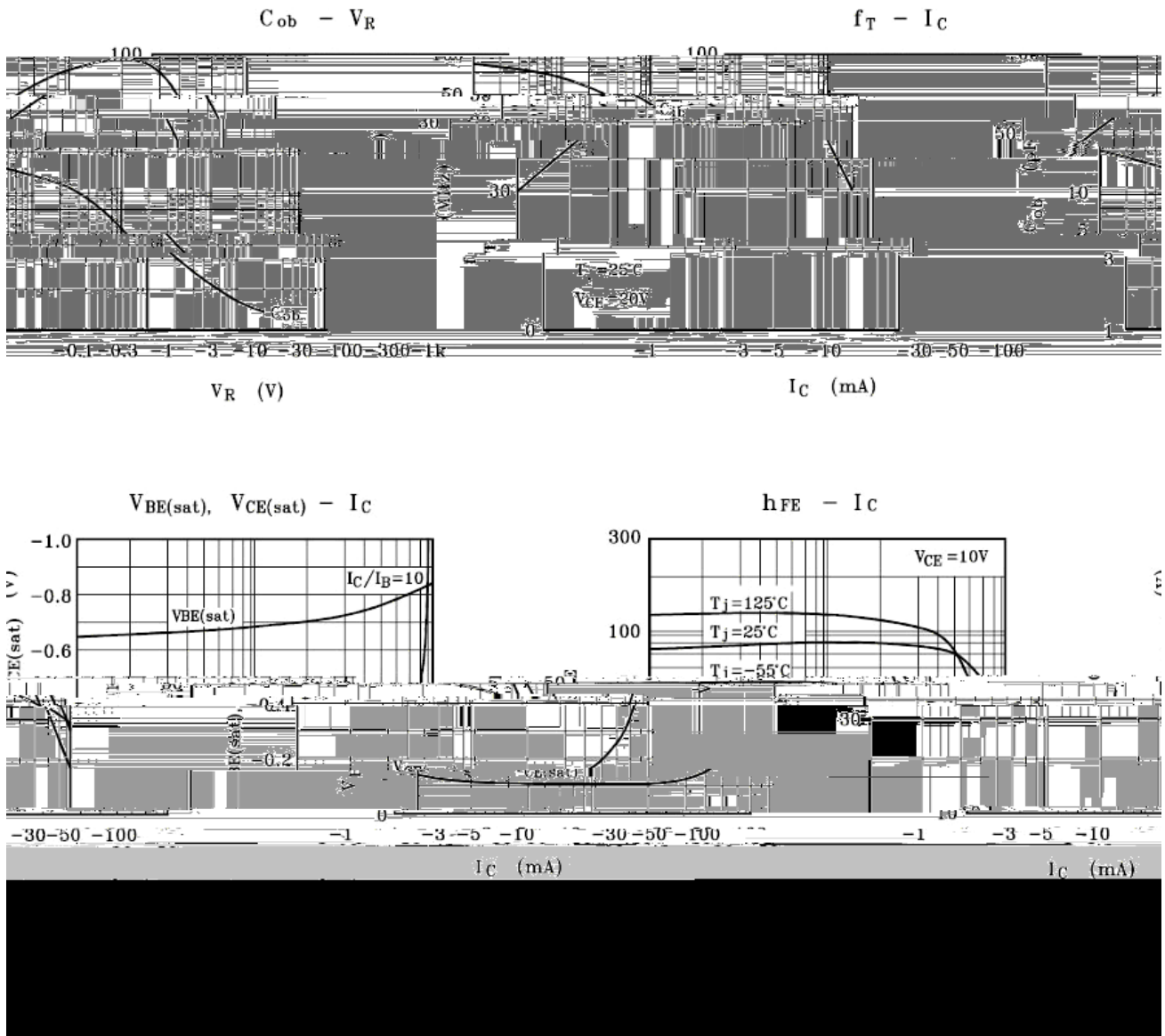




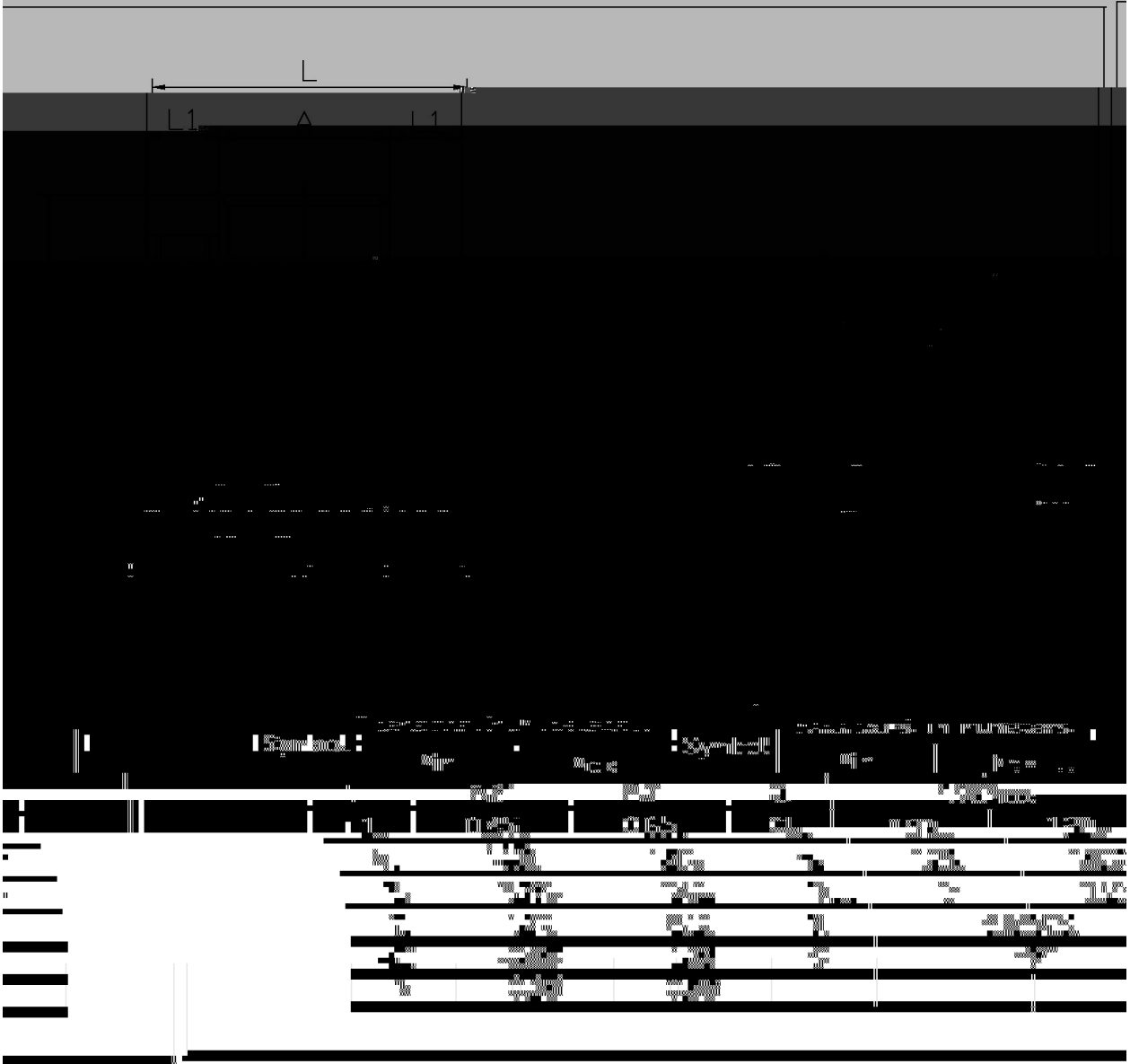
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	-300	V
Collector to Emitter Voltage	$V_{CEO}$	-300	V
Emitter to Base Voltage	$V_{EBO}$	-5.0	V
Collector Current	$I_C$	-500	mA
Collector Power Dissipation	$P_C$	350	mW
Junction Temperature	$T_j$	150	
Storage Temperature Range	$T_{stg}$	-55 150	

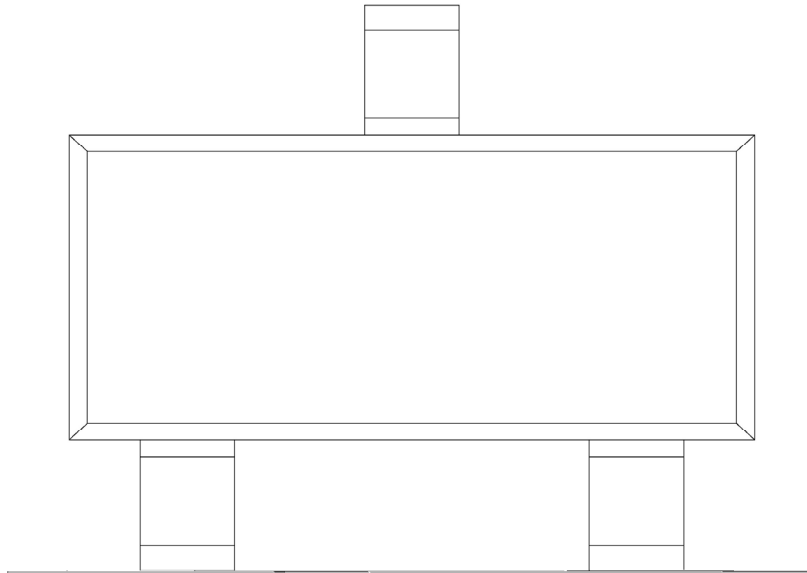
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	$V_{CBO}$	$I_C=-100mA$ $I_E=0$	-300			V
Collector to Emitter Breakdown Voltage	$V_{CEO}$	$I_C=-1.0mA$ $I_B=0$	-300			V
Emitter to Base Breakdown Voltage	$V_{EBO}$	$I_E=-100\mu A$ $I_C=0$	-5.0			V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=-200V$ $I_E=0$			-0.25	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{BE}=-3.0V$ $I_C=0$			-0.1	$\mu A$
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-10V$ $I_C=-10mA$	40			
	$h_{FE(2)}$	$V_{CE}=-10V$ $I_C=-30mA$	25			
	$h_{FE(3)}$	$V_{CE}=-10V$ $I_C=-1.0mA$	25			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-20mA$ $I_B=-2.0mA$			-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-20mA$ $I_B=-2.0mA$			-0.9	V
Transition Frequency	$f_T$	$V_{CE}=-20V$ $f=100MHz$ $I_C=-10mA$	50			MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=-20V$ $f=1.0MHz$ $I_E=0$			6.0	pF



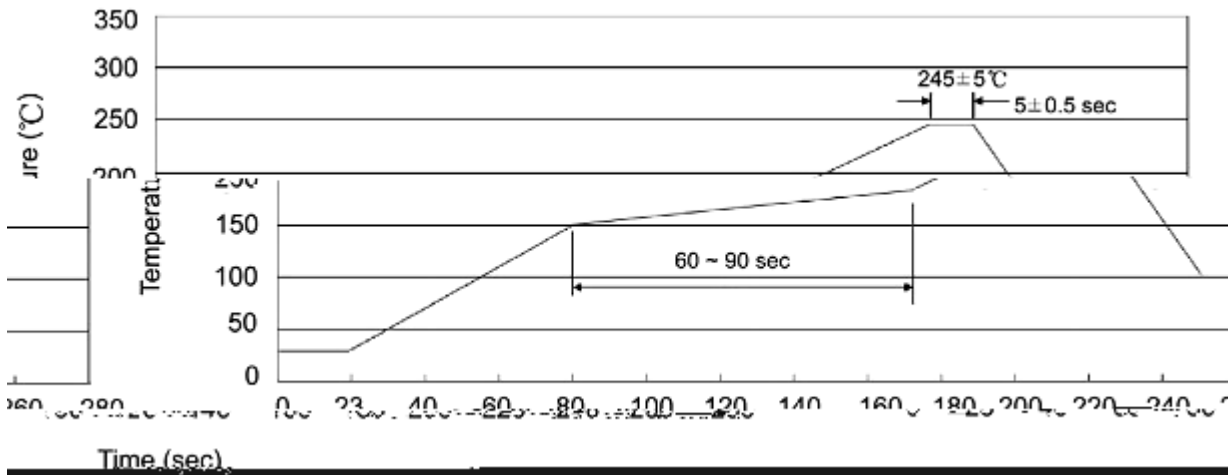
SOT-23

单位: mm





Rev.F Apr.-2017

**Temperature Profile for IR Reflow Soldering (Pb-Free)**


Note:

- |   |       |     |       |        |   |
|---|-------|-----|-------|--------|---|
| 1 | 25    | 150 | 60    | 90sec; | 1.Preheating:25~150 , Time:60~90sec.    |
| 2 | 245±5 |     | 5±0.5 | sec;   | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 |       | 2   | 10    | /sec.  | 3. Cooling Speed: 2~10 /sec.            |

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205